

# Rong Jiang

## List of Publications by Year in descending order

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528  
citing authors

#	ARTICLE	IF	CITATIONS
1	Effects of Applied Bias and High Field Stress on the Radiation Response of GaN/AlGa <sub>0.2</sub> N HEMTs. IEEE Transactions on Nuclear Science, 2015, 62, 2423-2430.	2.0	84
2	Charge Trapping in Al <sub>0.2</sub> O <sub>3</sub> /SiO <sub>2</sub> -Ga <sub>0.2</sub> O <sub>3</sub> -Based MOS Capacitors. IEEE Electron Device Letters, 2018, 39, 1022-1025.	3.9	50
3	Multiple Defects Cause Degradation After High Field Stress in AlGa <sub>0.2</sub> N/GaN HEMTs. IEEE Transactions on Device and Materials Reliability, 2018, 18, 364-376.	2.0	49
4	Worst-Case Bias for Proton and 10-keV X-Ray Irradiation of AlGa <sub>0.2</sub> N/GaN HEMTs. IEEE Transactions on Nuclear Science, 2017, 64, 218-225.	2.0	46
5	1/f Noise in As-Processed and Proton-Irradiated AlGa <sub>0.2</sub> N/GaN HEMTs Due to Carrier Number Fluctuations. IEEE Transactions on Nuclear Science, 2017, 64, 181-189.	2.0	31
6	Total-Ionizing-Dose Effects and Low-Frequency Noise in 30-nm Gate-Length Bulk and SOI FinFETs With SiO <sub>2</sub> /HfO <sub>2</sub> Gate Dielectrics. IEEE Transactions on Nuclear Science, 2020, 67, 245-252.	2.0	29
7	Dose-Rate Dependence of the Total-Ionizing-Dose Response of GaN-Based HEMTs. IEEE Transactions on Nuclear Science, 2019, 66, 170-176.	2.0	24
8	Degradation and annealing effects caused by oxygen in AlGa <sub>0.2</sub> N/GaN high electron mobility transistors. Applied Physics Letters, 2016, 109, .	3.3	22
9	Understanding Charge Collection Mechanisms in InGaAs FinFETs Using High-Speed Pulsed-Laser Transient Testing With Tunable Wavelength. IEEE Transactions on Nuclear Science, 2017, 64, 2069-2078.	2.0	17
10	Gate Bias and Length Dependences of Total Ionizing Dose Effects in InGaAs FinFETs on Bulk Si. IEEE Transactions on Nuclear Science, 2019, 66, 1599-1605.	2.0	17
11	Comparison of Total-Ionizing-Dose Effects in Bulk and SOI FinFETs at 90 and 295 K. IEEE Transactions on Nuclear Science, 2019, 66, 911-917.	2.0	17
12	Low-frequency noise and defects in copper and ruthenium resistors. Applied Physics Letters, 2019, 114, .	3.3	13
13	Capacitance-Frequency Estimates of Border-Trap Densities in Multifin MOS Capacitors. IEEE Transactions on Nuclear Science, 2018, 65, 175-183.	2.0	12
14	Total-Ionizing-Dose Responses of GaN-Based HEMTs With Different Channel Thicknesses and MOSHEMTs With Epitaxial MgCaO as Gate Dielectric. IEEE Transactions on Nuclear Science, 2018, 65, 46-52.	2.0	12
15	Worst-Case Bias for High Voltage, Elevated-Temperature Stress of AlGa <sub>0.2</sub> N/GaN HEMTs. IEEE Transactions on Device and Materials Reliability, 2020, 20, 420-428.	2.0	12
16	Total Ionizing Dose Effects in 70-GHz Bandwidth Photodiodes in a SiGe Integrated Photonics Platform. IEEE Transactions on Nuclear Science, 2019, 66, 125-133.	2.0	11
17	Total Ionizing Dose (TID) Effects in Ultra-Thin Body Ge-on-Insulator (GOI) Junctionless CMOSFETs With Recessed Source/Drain and Channel. IEEE Transactions on Nuclear Science, 2017, 64, 176-180.	2.0	10
18	Total-Ionizing-Dose Response of MoS <sub>2</sub> Transistors With ZrO <sub>2</sub> and h-BN Gate Dielectrics. IEEE Transactions on Nuclear Science, 2019, 66, 1584-1591.	2.0	6

#	ARTICLE	IF	CITATIONS
19	Total ionizing dose effects in passivated and unpassivated AlGaIn/GaN HEMTs. , 2016, , .		4
20	Total Ionizing Dose (TID) Effects in GaAs MOSFETs With La-Based Epitaxial Gate Dielectrics. IEEE Transactions on Nuclear Science, 2017, 64, 164-169.	2.0	4
21	Total-Ionizing-Dose Response of Nb <sub>2</sub> O <sub>5</sub> -Based MIM Diodes for Neuromorphic Computing Applications. IEEE Transactions on Nuclear Science, 2018, 65, 78-83.	2.0	4
22	1/f noise in GaN/AlGaIn HEMTs. , 2016, , .		2